

STATUS OF THE CLAIMS

The status of the claims of the present application stands as follows:

1. **(Currently amended)** A bipolar device, comprising:
 - (a) a substrate having a collector;
 - (b) an undoped epitaxial layer formed above said substrate at least above said collector;
 - (c) a doped epitaxial extrinsic base layer confronting said undoped epitaxial layer and having an aperture formed therein, said doped epitaxial extrinsic base layer including a remnant oxidated ring immediately surrounding said aperture;
 - (d) an emitter having a lower portion located in said aperture and confronting said undoped epitaxial layer; and
 - (e) a conductor ring formed in said doped epitaxial extrinsic ~~based~~ base layer surrounding said lower portion of said emitter.
2. **(Previously presented)** A bipolar device according to claim 1, further comprising a doped epitaxial intrinsic base layer located between said undoped epitaxial layer and said substrate.
3. **(Previously presented)** A bipolar device according to claim 1, wherein said emitter includes an upper portion distal from said substrate and extending over a portion of said doped epitaxial extrinsic base layer, said conductor ring extending radially out from underneath said upper portion.
4. **(Previously presented)** A bipolar device according to claim 1, wherein said conductor ring comprises a silicidated region of said doped epitaxial extrinsic base layer.
5. **(Previously presented)** A bipolar device according to claim 1, wherein said doped epitaxial extrinsic base layer has a thickness and said conductor ring has a thickness less than the thickness of said doped epitaxial extrinsic base layer.
6. **(Previously presented)** A bipolar device according to claim 1, wherein said remnant oxidated ring is perfectly symmetrical about said aperture.
7. **(Previously presented)** A bipolar device, comprising:

- (a) a substrate having a collector formed therein;
 - (b) a doped epitaxial intrinsic base layer formed on said substrate;
 - (c) an undoped epitaxial layer formed on said doped epitaxial intrinsic base layer;
 - (d) a doped epitaxial extrinsic base layer formed on said undoped epitaxial layer and including an aperture and a remnant oxidated ring immediately surrounding said aperture;
 - (e) an emitter including a lower portion and an upper portion, said lower portion being located in said aperture and said upper portion being located above said lower portion and extending over a portion of said doped epitaxial extrinsic base layer; and
 - (f) a conductor formed in said doped epitaxial extrinsic base layer and located both underneath a portion of said upper portion of said emitter and out from underneath said upper portion of said emitter.
8. **(Previously presented)** A bipolar device according to claim 7, wherein said remnant oxidated ring is perfectly symmetrical about said aperture.
9. **(Previously presented)** A bipolar device according to claim 7, wherein said conductor comprises a silicidated region of said doped epitaxial extrinsic base layer.
10. **(Previously presented)** A bipolar device, comprising:
- (a) a substrate having a collector;
 - (b) an undoped epitaxial layer formed above said substrate at least above said collector;
 - (c) a doped epitaxial extrinsic base layer confronting said undoped epitaxial layer and having an aperture formed therein;
 - (d) an emitter having a lower portion located in said aperture and confronting said undoped epitaxial layer;
 - (e) a conductor ring formed in said doped epitaxial extrinsic based layer surrounding said lower portion of said emitter; and
 - (f) an emitter trench etch landing pad remnant located on said doped epitaxial extrinsic base layer immediately surrounding said aperture.
11. **(Previously presented)** A bipolar device according to claim 10, further comprising a nitride spacer located on top of said landing pad remnant.

Claims 12-20: (Canceled)

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